

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2000-319772

(43)Date of publication of application : 21.11.2000

(51)Int.Cl.

C23C 14/24

(21)Application number : 11-268198

(71)Applicant : P K LTD

(22)Date of filing : 22.09.1999

(72)Inventor : HYUN KWANG-SOO  
PARK KYUNG-HO  
YOON NEUNG-GOO  
CHOI KANG-JUN  
JEONG SOO-HONG

(30)Priority

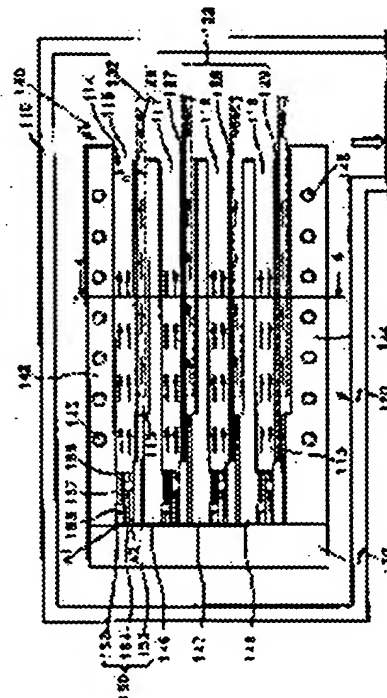
Priority number : 99 9915805 Priority date : 01.05.1999 Priority country : KR

(54) ATOMIC LAYER VAPOR DEPOSITION DEVICE CAPABLE OF VAPOR- DEPOSITING THIN FILM ON PLURAL SUBSTRATE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide an atomic layer vapor deposition device capable of vapor- depositing thin films on plural substrates.

SOLUTION: This vapor deposition device is provided with a vacuum chamber 110 and a reactor 120 provided at the inside of the vacuum chamber. The reactor is provided with separable plural modules 140 and a gas feeding part 130. By assembling the modules, an opening A and plural stages 114 for storing substrates are formed. Reaction gas and purge gas are fed from the gas feeding part 130 into the reactor. Gas feeding lines 150 for pouring each gas into the stage parts are formed at the modules. By this vapor deposition device, thin films having good properties can be vapor-deposited on plural substrates having fine patterns at one time.



## LEGAL STATUS

[Date of request for examination] 22.09.1999

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]